



Designation: E983 – 19

Standard Guide for Minimizing Unwanted Electron Beam Effects in Auger Electron Spectroscopy¹

This standard is issued under the fixed designation E983; the number immediately following the designation indicates the year of original adoption or, in the case of revision, the year of last revision. A number in parentheses indicates the year of last reapproval. A superscript epsilon (ϵ) indicates an editorial change since the last revision or reapproval.

1. Scope

1.1 This guide outlines the origins and manifestations of unwanted electron beam effects in Auger electron spectroscopy (AES).

1.2 Some general guidelines are provided concerning the electron beam parameters which are most likely to produce these effects and suggestions are offered on how to minimize them.

1.3 General classes of materials are identified which are most likely to exhibit unwanted electron beam effects. In addition, a tabulation of some specific materials which have been observed to undergo electron damage effects is provided.

1.4 A simple method is outlined for establishing the existence and extent of these effects during routine AES analysis.

1.5 The values stated in SI units are to be regarded as standard. No other units of measurement are included in this standard.

1.6 *This standard does not purport to address all of the safety concerns, if any, associated with its use. It is the responsibility of the user of this standard to establish appropriate safety, health, and environmental practices and determine the applicability of regulatory limitations prior to use.*

1.7 *This international standard was developed in accordance with internationally recognized principles on standardization established in the Decision on Principles for the Development of International Standards, Guides and Recommendations issued by the World Trade Organization Technical Barriers to Trade (TBT) Committee.*

2. Referenced Documents

2.1 *ASTM Standards:*²

¹ This guide is under the jurisdiction of ASTM Committee E42 on Surface Analysis and is the direct responsibility of Subcommittee E42.03 on Auger Electron Spectroscopy and X-Ray Photoelectron Spectroscopy.

Current edition approved April 1, 2019. Published May 2019. Originally approved in 1984. Last previous edition approved in 2018 as E983–10 (2018). DOI: 10.1520/E0983–19.

² For referenced ASTM standards, visit the ASTM website, www.astm.org, or contact ASTM Customer Service at service@astm.org. For *Annual Book of ASTM Standards* volume information, refer to the standard's Document Summary page on the ASTM website.

[E673 Terminology Relating to Surface Analysis](#) (Withdrawn 2012)³

[E996 Practice for Reporting Data in Auger Electron Spectroscopy and X-ray Photoelectron Spectroscopy](#)

2.2 *ISO Standard:*⁴

[ISO 18115-1:2013 Surface chemical analysis -- Vocabulary -- Part 1: General terms and terms used in spectroscopy](#)

3. Terminology

3.1 See ISO 18115-1:2013 for terms used in Auger electron spectroscopy.

NOTE 1—Electron beam effects and their consequences are widely referred to in the literature using any one or more of the following terms: electron beam damage, sample damage, specimen damage, beam effects, electron beam induced processes, and electron irradiation effects.

4. Significance and Use

4.1 When electron beam excitation is used in AES, the incident electron beam can interact with the specimen material causing physical and chemical changes. In general, these effects are a hindrance to AES analysis because they cause localized specimen modification **(1-4)**.⁵

4.2 With specimens that have poor electrical conductivity the electron beam can stimulate the development of localized charge on the specimen surface. This effect is a hindrance to AES analysis because the potentials associated with the charge can either adversely affect the integrity of Auger data or make Auger data collection difficult **(5, 6)**.

5. Origins of Electron Beam Effects

5.1 Electron beam effects in AES may originate from one or more distinct processes.

5.1.1 Charge accumulation **(7)** (see Chapter 9) in materials with poor electrical conductivity leading to potentials that cause distortion of Auger data or make AES data collection difficult by virtue of:

³ The last approved version of this historical standard is referenced on www.astm.org.

⁴ Available from International Organization for Standardization (ISO), ISO Central Secretariat, BIBC II, Chemin de Blandonnet 8, CP 401, 1214 Vernier, Geneva, Switzerland, <http://www.iso.org>.

⁵ The boldface numbers in parentheses refer to the references listed at the end of this standard.

- 5.1.1.1 Auger peak shift on energy scale,
- 5.1.1.2 Auger peak shape and size distortion, and
- 5.1.1.3 Auger signal strength instability.
- 5.1.2 Electronic excitation of surface, subsurface, and bulk atoms and molecules leading to specimen changes (8-10) which include:
 - 5.1.2.1 Dissociation,
 - 5.1.2.2 Electron stimulated desorption (ESD) (11),
 - 5.1.2.3 Electron stimulated adsorption (ESA) (12),
 - 5.1.2.4 Polymerization (13, 14),
 - 5.1.2.5 Carburization (15-17),
 - 5.1.2.6 Oxidation (18, 19),
 - 5.1.2.7 Reduction (20),
 - 5.1.2.8 Decomposition (21, 22),
 - 5.1.2.9 Erosion, and
 - 5.1.2.10 Diffusion.
- 5.1.3 Charge accumulation in materials of poor electrical conductivity leading to specimen changes which include (23, 24, 7) (see Chapter 8):
 - 5.1.3.1 Electric field enhanced diffusion, and
 - 5.1.3.2 Electromigration (4) (see p. 62).
- 5.1.4 Heating which may cause:
 - 5.1.4.1 Annealing,
 - 5.1.4.2 Segregation,
 - 5.1.4.3 Volatilization, and
 - 5.1.4.4 Chemical reaction.

6. Practical Manifestations of Electron Beam Effects

- 6.1 Electron dose dependent changes in the intensity, energy, or peak shape of one or more Auger transitions, or any combination thereof; depending upon the material, these changes may be complete within a fraction of a second or they may progress for hours.
- 6.2 Discoloration of the specimen in the proximity of the electron beam irradiated region.
- 6.3 Physical damage to the specimen such as erosion, cracking, blistering, or densification.
- 6.4 Pressure rises in the analytical vacuum chamber during electron irradiation.
- 6.5 Localized electric charge dependent changes in the intensity, energy, or peak shape of all Auger transitions, or any combination thereof. These changes may be stable but often are erratic resulting in unstable AES signals which may preclude AES data collection.

7. Electron Beam Parameters

7.1 Electron Dose and Current Density:

7.1.1 Electron dose and current density were previously defined using units of C/cm^2 and mA/cm^2 , respectively. These units are not consistent with the SI system. To keep from changing the magnitude of the numbers appearing in the literature (from which Table 1 is adapted), the multipliers of the terms are being changed. A dose of C/cm^2 is equivalent to $10^4 C/m^2$, while $1mA/cm^2$ is equivalent to $10A/m^2$.

7.1.2 Specimen material modification can often be related to the electron dose (D); that is, the number of electrons incident

TABLE 1 Electron Beam Damage in AES^A

Material	Incident Beam Energy, keV	D_c , $10^4 C/m^2$	T	Refs
Si_3N_4	2	stable	...	(25)
Al_2O_3	5	10	3 h	(2)
Cu, Fe	1	1	15 min	(26)
Phthalocyanines				
SiO_2	2	0.6	10 min	(25)
Li_2WO_4	1	0.05	8 min	(27)
NaF, LiF	0.1	0.06	60 s	(22)
$LiNO_3$, $LiSO_4$	1	0.05	50 s	(27)
KCl	1.5	0.03	30 s	(22)
TeO_2	2	0.02	20 s	(28)
$H_2O(F)$	1.5	0.01	10 s	(29)
Native oxides	5	2×10^{-3}	2 s	(3)
$C_6H_{12}(F)$	0.1	3×10^{-4}	0.3 s	(30)
Na_3AlF_6	3	$10^{-4} - 10^{-3}$	0.1 s	(31)
$CH_3OH(F)$	1.5	2.5×10^{-4}	0.3 s	(29)

A

where:

D_c = critical dose for detectable damage,

T = time of electron bombardment at $10A/m^2$ without detectable damage, and

F = frozen.

(Adapted from Ref. 1.)

on a unit area of the specimen, expressed in coulombs per square centimeter (C/cm^2) (1).

7.1.3 A number of materials, (for example, see Table 1), exhibit dose-dependent effects when the electron dose exceeds a material specific critical dose, D_c . The magnitude of the critical dose corresponds to the onset of detectable damage and the values may be subject to future revision. The material specific critical dose, D_c , may be as low as $1 C/m^2$.

7.1.4 In practice, the electron dose is directly dependent upon the electron beam current density, J_B , (A/m^2), the time of electron irradiation in seconds, $t(s)$; and the angle of incidence, Θ , of the beam on the sample. That is, $D_c(C/m^2) = J_B(A/m^2) \cdot t(s) \cdot \cos\Theta$. Using a typical electron beam current density, $10 A/m^2$ would be equivalent to using $10^{-8} A$ incident beam current into a $33 \mu m$ electron beam diameter at normal incidence.

7.1.5 The electron beam-induced heating of a given material of poor thermal conductivity and the accumulation of charge on a material of poor electrical conductivity are dependent upon the electron beam current density.

7.1.6 Current densities for a static electron beam should be of the order $10^4 A/m^2$ or less for susceptible materials. In the case of rastered or gated electron beams, the time-averaged current density and the instantaneous current density must be considered. Even though the time-averaged current density may be small, the instantaneous current density may be sufficient to cause specimen damage or specimen charging.

7.1.7 In small-spot AES analysis, or scanning Auger microscopy, the use of electron probes with high current density is inherent. Obviously a trade-off between signal-to-noise and the perturbing effects of the electron beam is required (2).